



# PSMN8R5-100PSF

NextPower 100 V, 8.7 mΩ N-channel MOSFET in TO220 package

10 April 2017

Product data sheet

## 1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

## 2. Features and benefits

- Optimised for fast switching, low spiking, high efficiency
- Low  $Q_G \times R_{DSon}$  FOM for high efficiency switching applications
- Low body diode losses ( $Q_{rr}$ ) and fast recovery ( $t_{rr}$ )
- Strong avalanche energy rating ( $E_{AS}$ )
- Avalanche rated & 100% tested
- Ha-free & RoHS compliant TO220 package

## 3. Applications

- Synchronous rectification in AC-to-DC and DC-to-DC applications
- Brushed & BLDC motor control
- UPS & solar inverter
- LED lighting
- Battery protection
- Full-bridge & half-bridge applications
- Flyback & resonant topologies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$		-	-	100	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	[1]	-	-	98	A
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>		-	-	183	W
$T_j$	junction temperature			-55	-	175	$^\circ\text{C}$
<b>Static characteristics</b>							
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	7.5	8.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	11.2	13.5	mΩ
<b>Dynamic characteristics</b>							
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	8.7	-	nC
$Q_{G(tot)}$	total gate charge			-	44.5	-	nC

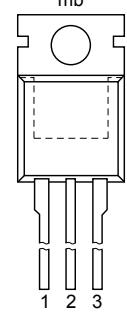
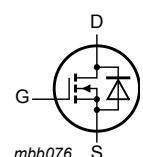
**nexperia**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 34 \text{ A}$ ; $V_{sup} \leq 100 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $T_{J(init)} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 4</a> ; Unclamped	[2]	-	-	281	mJ

[1] Avalanche current is limited by  $I_{AS}$   
 [2] Protected by 100% test

## 5. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain	 <b>TO-220AB (SOT78)</b>	

## 6. Ordering information

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PSMN8R5-100PSF	TO-220AB	plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body	SOT78

## 7. Marking

**Table 4. Marking codes**

Type number	Marking code
PSMN8R5-100PSF	PSMN8R5-100PSF

## 8. Limiting values

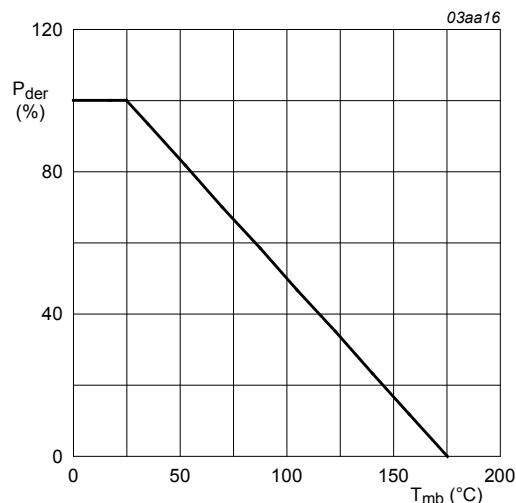
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25^{\circ}\text{C} \leq T_j \leq 175^{\circ}\text{C}$		-	100	V
$V_{DGR}$	drain-gate voltage	$25^{\circ}\text{C} \leq T_j \leq 175^{\circ}\text{C}; R_{GS} = 20\text{ k}\Omega$		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
$P_{\text{tot}}$	total power dissipation	$T_{mb} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 1</a>		-	183	W
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 2</a>	[1]	-	98	A
		$V_{GS} = 10\text{ V}; T_{mb} = 100^{\circ}\text{C}$ ; <a href="#">Fig. 2</a>		-	69	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 3</a>		-	391	A
$T_{\text{stg}}$	storage temperature			-55	175	°C
$T_j$	junction temperature			-55	175	°C
$T_{\text{sld(M)}}$	peak soldering temperature			-	260	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25^{\circ}\text{C}$		-	98	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25^{\circ}\text{C}$		-	391	A
<b>Avalanche ruggedness</b>						
$E_{DS(\text{AL})S}$	non-repetitive drain-source avalanche energy	$I_D = 34\text{ A}; V_{\text{sup}} \leq 100\text{ V}; R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25^{\circ}\text{C}$ ; <a href="#">Fig. 4</a> ; Unclamped	[2]	-	281	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{\text{sup}} \leq 100\text{ V}; V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25^{\circ}\text{C}$ ; $R_{GS} = 50\text{ }\Omega$	[2]	-	34	A

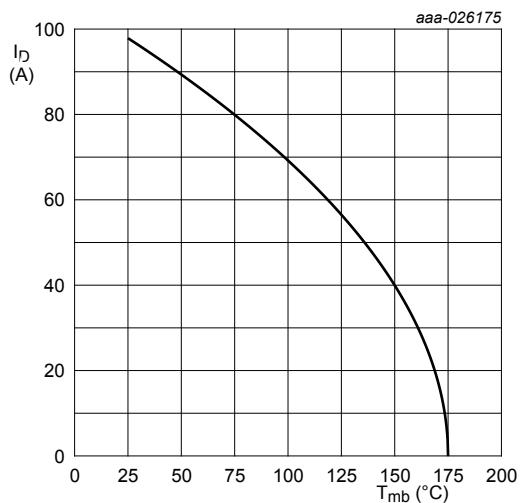
[1] Avalanche current is limited by  $I_{AS}$

[2] Protected by 100% test

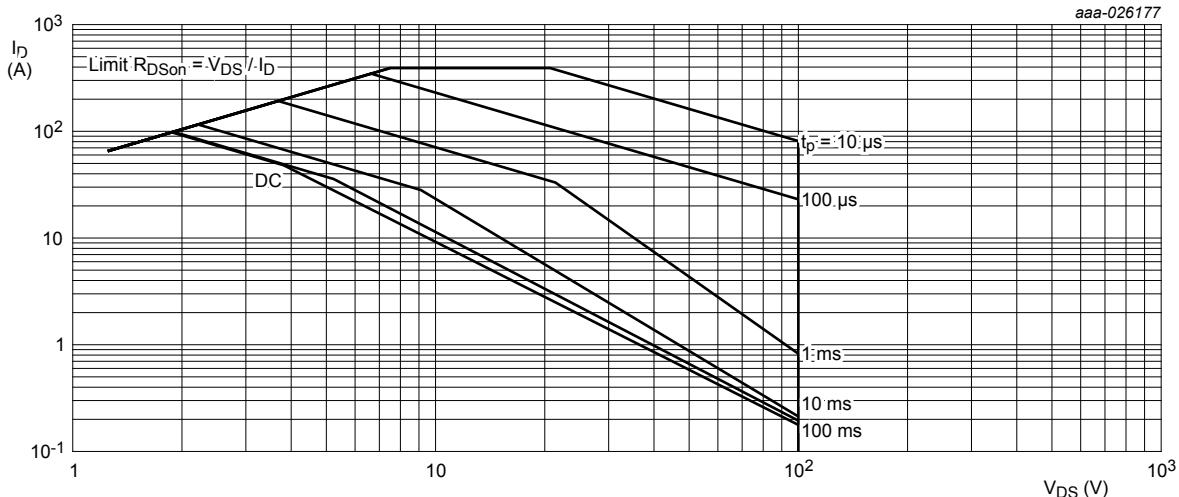


$$P_{der} = \frac{P_{tot}}{P_{tot}(25^\circ\text{C})} \times 100 \%$$

**Fig. 1. Normalized total power dissipation as a function of mounting base temperature**

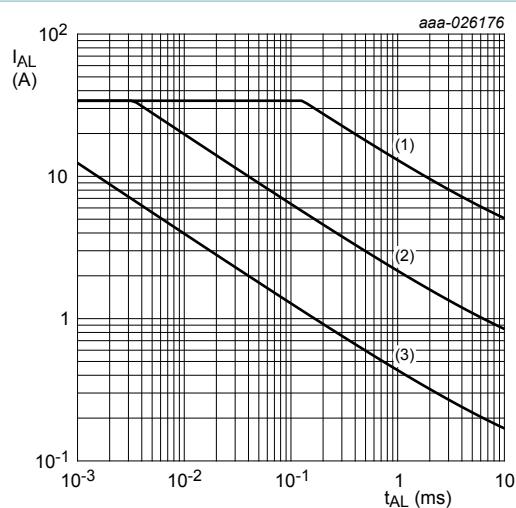


**Fig. 2. Continuous drain current as a function of mounting base temperature**



$T_{mb} = 25^\circ\text{C}$ ;  $I_{DM}$  is a single pulse

**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**



(1)  $T_j$  (init) = 25 °C; (2)  $T_j$  (init) = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 5</a>	-	0.71	0.82	K/W

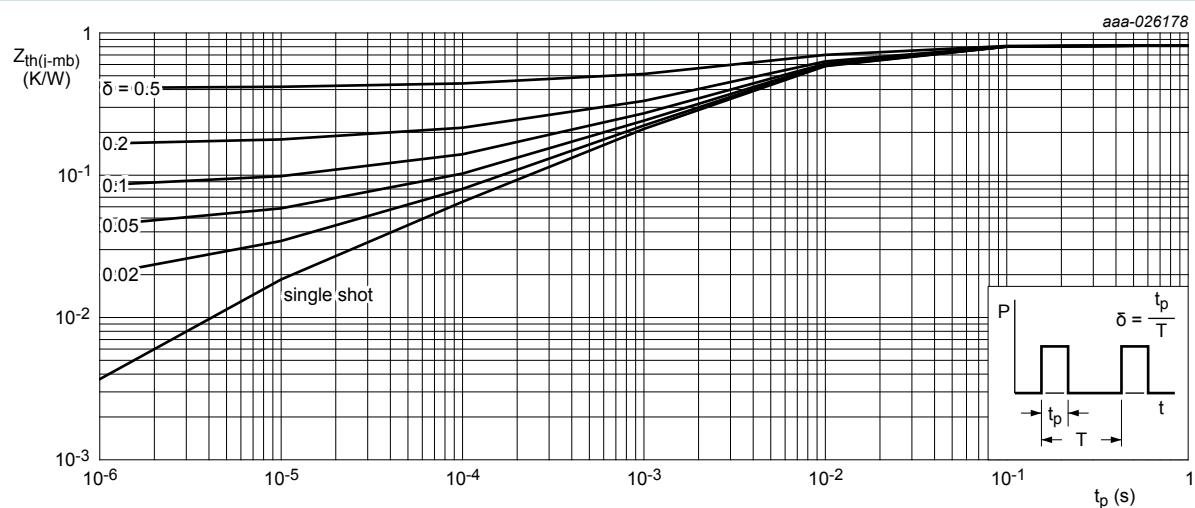


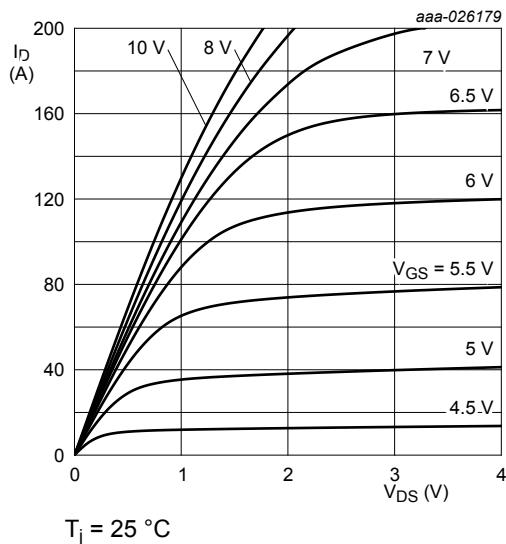
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

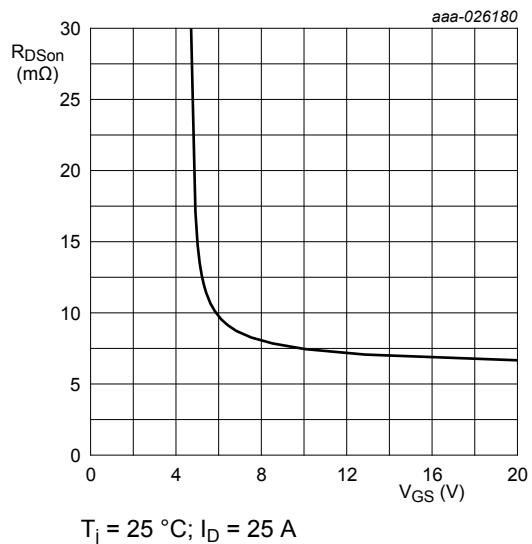
**Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 µA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		100	-	-	V
		I <sub>D</sub> = 250 µA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C		90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C		-	3.6	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C		-	1.8	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>		2	3.1	4	V
ΔV <sub>GS(th)/ΔT</sub>	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-8.4	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.05	1	µA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C		-	-	100	µA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	5	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	5	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	7.5	8.7	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	8.9	13.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; <a href="#">Fig. 11</a>		-	11.2	13.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <a href="#">Fig. 11</a>		-	16	19	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz		-	1.54	-	Ω
<b>Dynamic characteristics</b>							
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	44.5	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V		-	22.9	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	14.5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge			-	8.8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge			-	5.6	-	nC
Q <sub>GD</sub>	gate-drain charge			-	8.7	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	4.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a>		-	3181	-	pF
C <sub>oss</sub>	output capacitance			-	551	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	12	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C		-	16.8	-	ns
t <sub>r</sub>	rise time			-	26.8	-	ns

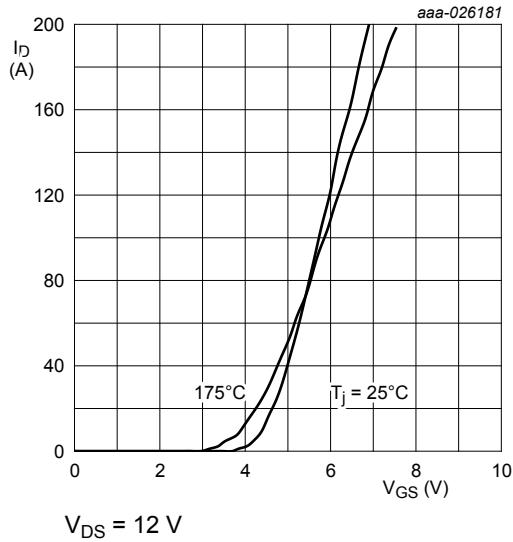
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$t_{d(\text{off})}$	turn-off delay time			-	31.5	-	ns
$t_f$	fall time			-	23.6	-	ns
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C}$ ; <a href="#">Fig. 15</a>		-	0.83	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$ ; <a href="#">Fig. 16</a>		-	51	-	ns
$Q_r$	recovered charge			-	70	-	nC



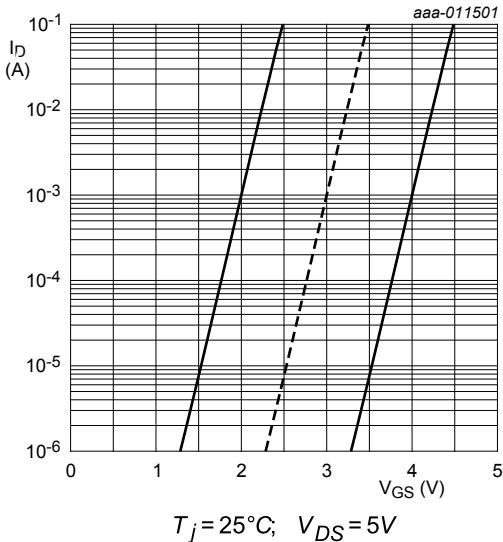
**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



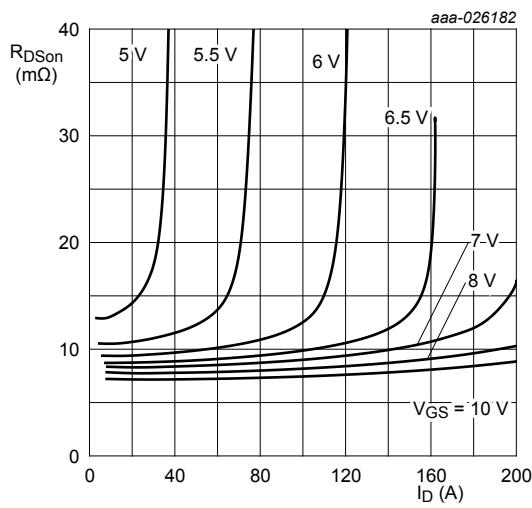
**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**



**Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

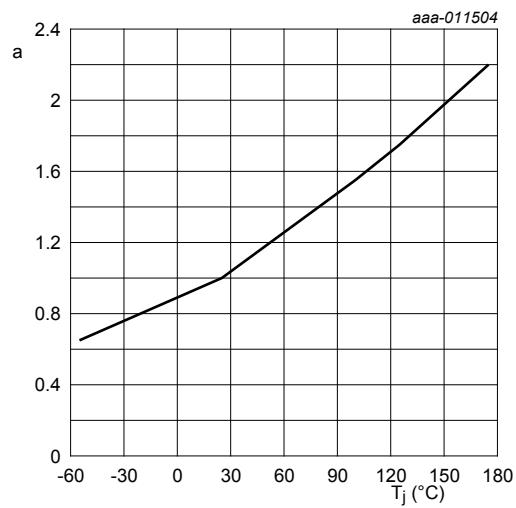


**Fig. 9. Sub-threshold drain current as a function of gate-source voltage**



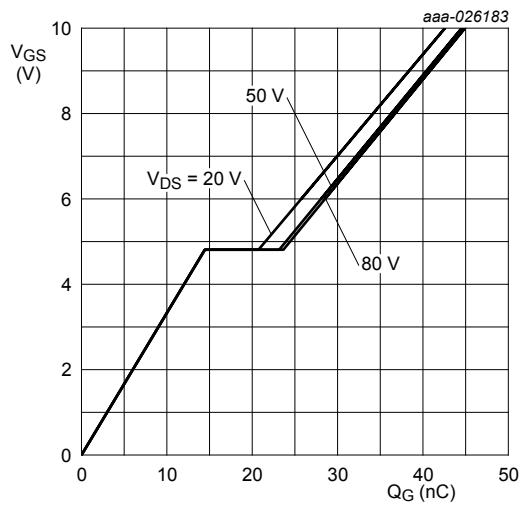
$T_j = 25^\circ\text{C}$

Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon} (25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature



$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

Fig. 12. Gate-source voltage as a function of gate charge; typical values

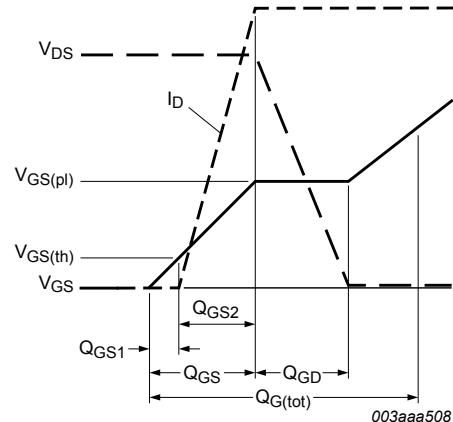
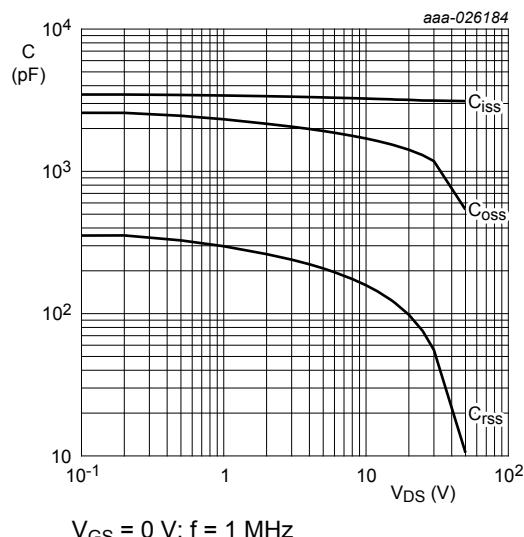
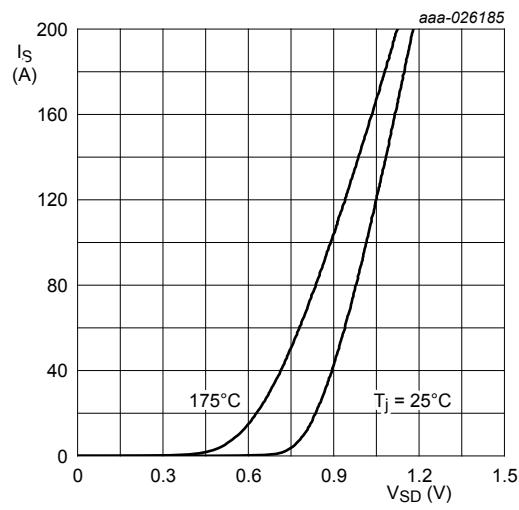


Fig. 13. Gate charge waveform definitions



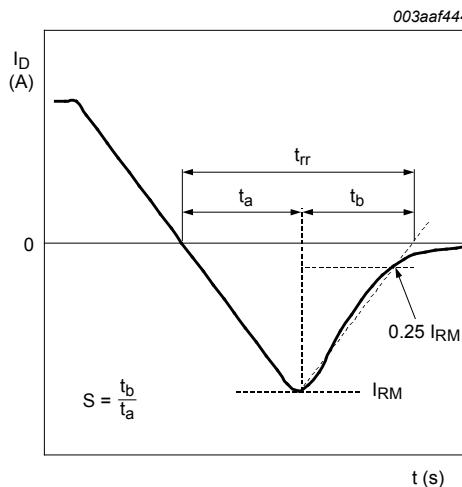
$V_{GS} = 0$  V;  $f = 1$  MHz

**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



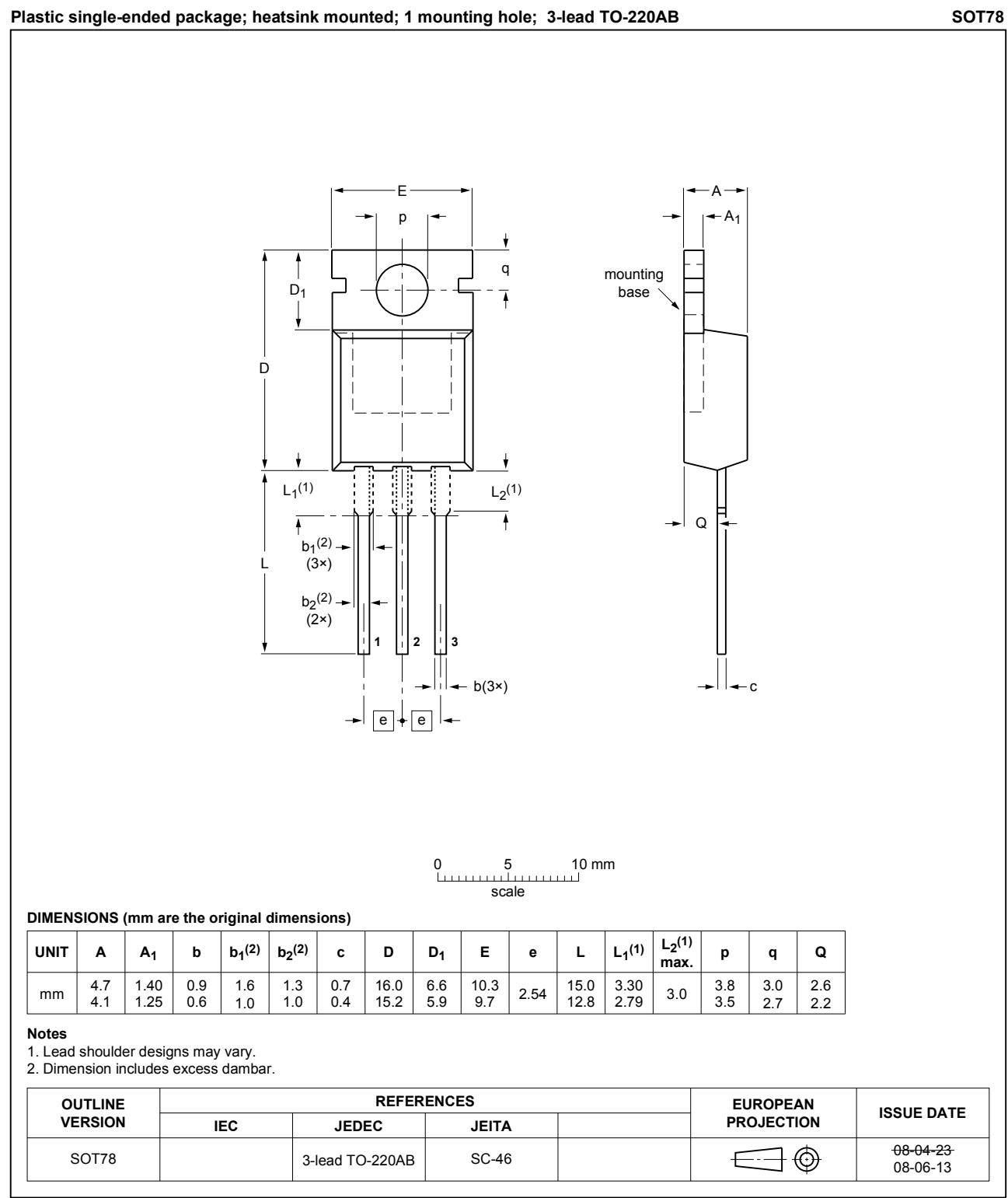
$V_{GS} = 0$  V

**Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values**



**Fig. 16. Reverse recovery timing definition**

## 11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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